NSN 5961-01-181-2667

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Inclosure Material:

Metal

Overall Length:

1.573 inches

Overall Height:

0.420 inches

Overall Width:

1.050 inches

Mounting Facility Quantity:

2

Internal Configuration:

Field effect

Mounting Method:

Unthreaded hole

Features Provided:

Hermetically sealed case and quality assurance level tx

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

100.0 drain to source voltage and 100.0 drain to gate voltage and 20.0 gate to source voltage

Current Rating Per Characteristic:

24.00 amperes dark current and 38.00 amperes off-state current, peak

Power Rating Per Characteristic:

1.2 watts total power dissipation

Maximum Operating Tempurature Per Measurement Point:

150.0 degrees celsius junction

Test Data Document:

81349-mil-prf-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Terminal Type And Quantity:

2 unthreaded hole and 1 case

Specification Data:

81349-mil-prf-19500/543 government specification

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

A110a0

Mil-std (military Standard):

Mil-prf-19500 spec.